# ENSC 450 VLSI Design - Phase 02

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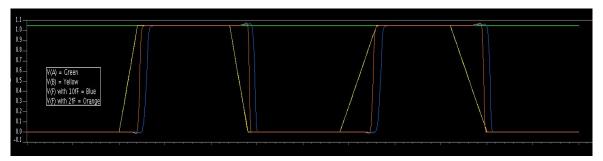
For Dr. Anita Tino and Sheida Alan

### Standard Cell Area and Capacitance

- Area of cell = (sum of transistor areas in cell) \* (drive strength) \* (unit area)
- Capacitance of cell = (single terminal input capacitance) \* (drive strength) \* (unit capacitance)
- Data values for worst case transitions for rise propagation delay Tpdr
  - o NOT: "1" to "0"
  - o NAND: "11" to "10"
  - o NOR: "10" to "00"
  - o AND: "10" to "11"

X1	NOT	NAND	NOR	AND	X4	NOT	NAND	NOR	AND
Area (um²)	3	8	10	11	Area (um²)	12	32	40	44
Gate Cap (fF)	3	4	5	4	Gate Cap (fF)	12	16	20	16

### AND\_X1 Results



```
*** parameter load =
                       2.000E-15 ***
and x1
 ***** transient analysis tnom= 25.000 temp= 125.000 *****
 tpdf 1ns= 5.7701E-10 targ= 1.2077E-08 trig= 1.1500E-08
 pdf 2ns= 8.2140E-10 targ= 2.4821E-08 trig= 2.4000E-08
 tpdr_1ns= 6.1136E-10 targ= 6.1114E-09 trig= 5.5000E-09
 tpdr_2ns= 8.0889E-10 targ= 1.8809E-08 trig= 1.8000E-08
 ttr Ins= 1.0123E-10 targ= 6.1602E-09 trig= 6.0589E-09
 ttr_2ns= 1.1450E-10 targ= 1.8860E-08
 ttf 1ns= 2.6928E-10 targ= 6.1000E-09 trig= 5.8308E-09
 ttf_2ns= 3.6217E-10 targ= 1.8812E-08 trig= 1.8450E-08
        ***** job concluded
 *** parameter load = 1.000E-14 ***
and x1
 ***** transient analysis tnom= 25.000 temp= 125.000 *****
 tpdf_1ns= 8.7823E-10 targ= 1.2378E-08 trig= 1.1500E-08
 pdf_2ns= 1.1617E-09 targ= 2.5162E-08 trig= 2.4000E-08
 tpdr 1ns= 9.8153E-10 targ= 6.4815E-09 trig= 5.5000E-09
 tpdr 2ns= 1.2075E-09 targ= 1.9207E-08
                                        trig= 1.8000E-08
 ttr_Ins= 1.6542E-10 targ= 6.5531E-09 trig= 6.3877E-09
 ttr 2ns= 1.6438E-10 targ= 1.9282E-08
                                        trig= 1.9118E-08
 ttf_1ns= 6.2630E-10 targ= 6.5939E-09
 ttf 2ns= 6.7341E-10 targ= 1.9321E-08
```

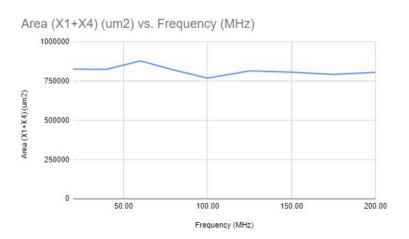
#### **HSpice Simulation:**

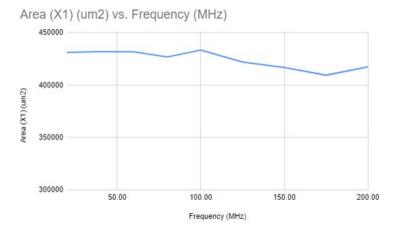
- $T_{tran} = 1$ ns,  $C_{load} = 2$ fF
- $T_{tran} = 1$ ns,  $C_{load} = 10$ fF
- $T_{tran} = 2ns, C_{load} = 2fF$
- $T_{tran} = 2ns, C_{load} = 10fF$
- Collected values for T<sub>ppe</sub>,  $T_{DDR}$ ,  $T_{tf}$ ,  $T_{tr}$

**Waveform Comments:** 

- C<sub>load</sub> = 2fF in Orange
- $C_{load} = 10$ fF in Blue
- Rise Transitions: '10' -> '11'
- Fall Transitions: '11' -> '10'
- Higher load capacitance results in slower transitions
- X1 vs X4:
- X4 cells had expected behaviour of less delay

### X1 and X1+X4 Area vs. Frequency





## Synthesis Result Comparison

Libraries Used	FreePDK	X1 only	X1 and X4	
Area (um²)	46,773	431,859	826,802	
Critical Path (ns)	Slack Met (0.14)	Slack Met (0.0)	Slack Met (0.67)	
Data Arrival (ns)	4.70	16.67	24.33	
Period (ns)	5	16.67	25	
Frequency	200 MHz	60 MHz	40 MHz	